

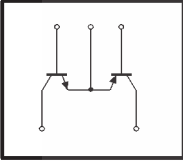
General purpose (dual transistors)

FMY5

●Features

- Both the 2SA1514K and 2SC3906K chips in an SMT package.
- PNP and NPN chips are connected in a common emitter configuration.

●Circuit diagram



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	120	V
Collector-emitter voltage	V _{CE0}	120	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	50	mA
Power dissipation	P _c	300 (TOTAL)	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55~+150	°C

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●Package, marking, and packaging specifications

Part No.	FMY5
Package	SMT5
Marking	Y5
Code	T148
Basic ordering unit (pieces)	3000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	120	—	—	V	I _c =50/-50 μA
Collector-emitter breakdown voltage	BV _{CE0}	120	—	—	V	I _c =1/-1mA
Emitter-base breakdown voltage	BV _{EB0}	5	—	—	V	I _e =50/-50 μA
Collector cutoff current	I _{cBO}	—	—	0.5	μA	V _{CB} =100/-100V
Emitter cutoff current	I _{eBO}	—	—	0.5	μA	V _{EB} =4/-4V
DC current transfer ratio	h _{FE}	120	—	820	—	V _{CE} =6/-6V, I _c =2/-2mA
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.5	V	I _c =10/-10mA, I _e =1/-0.1mA
Transition frequency	f _T	—	140	—	MHz	V _{CE} =12/-12V, I _e =2/-2mA, f=100MHz
Output capacitance	C _{ob}	—	3/4	—	pF	V _{CE} =12/-12V, I _e =0A, f=1MHz

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. *Transition frequency of the device.

(94S-440-AC1)

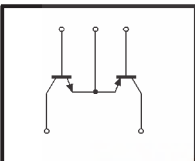
Totempoles (dual transistors)

FMY6

●Features

- Both the 2SA1036K and 2SC2411K chips in an SMT package.
- PNP and NPN chips are connected in a common emitter configuration.
- High I_{cmax}. (Max. 500mA)

●Circuit diagram



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	40	V
Collector-emitter voltage	V _{CE0}	32	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	500	mA
Power dissipation	P _d	300 (TOTAL)	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55~+150	°C

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●Package, marking, and packaging specifications

Part No.	FMY6
Package	SMT5
Marking	Y6
Code	T148
Basic ordering unit (pieces)	3000

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	40	—	—	V	I _c =100/-100 μA
Collector-emitter breakdown voltage	BV _{CE0}	32	—	—	V	I _c =1/-1mA
Emitter-base breakdown voltage	BV _{EB0}	5	—	—	V	I _e =100/-100 μA
Collector cutoff current	I _{cBO}	—	—	1	μA	V _{CB} =20/-20V
Emitter cutoff current	I _{eBO}	—	—	1	μA	V _{EB} =4/-4V
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.4	V	I _c =100/-100mA, I _B =10/-10mA
DC current transfer ratio	h _{FE}	120	—	—	—	V _{CE} /I _c =3/-3V, I _c =10/-10mA
Transition frequency	f _T	—	250/200	—	MHz	V _{CE} =5/-5V, I _e =20/-20mA, f=200MHz
Output capacitance	C _{ob}	—	6.5/7	—	pF	V _{CE} =10/-10V, I _e =0A, f=1MHz

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. *Transition frequency of mounted transistor.